

T-1 (3mm) INFRA-RED EMITTING DIODE

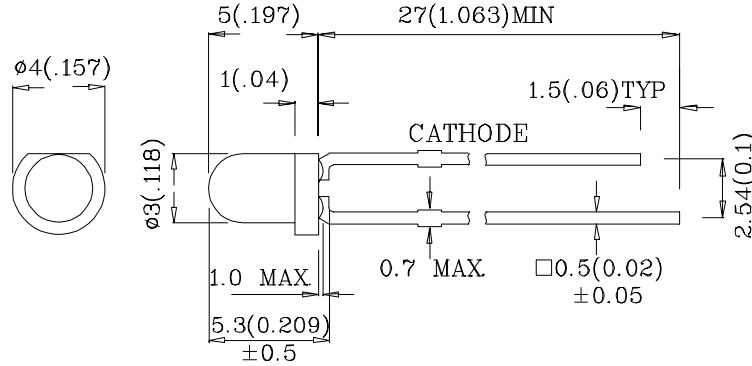
XTHI30BF850



SUN LED

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Notes:

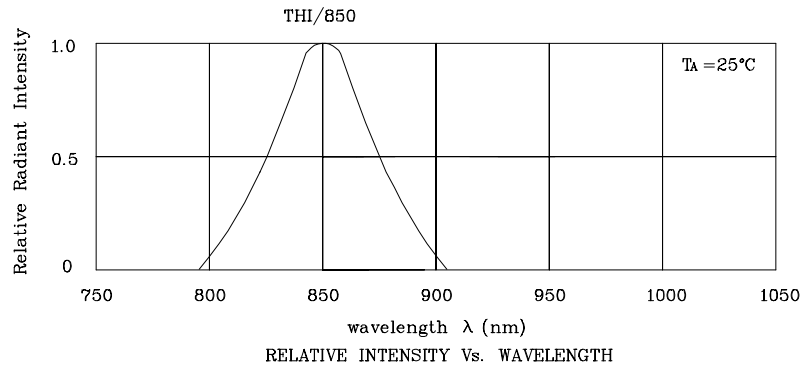
1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.

Absolute maximum ratings (T _A =25°C)		THI/850 (GaAlAs)	Unit
Reverse voltage	V _R	5	V
Forward current	I _F	50	mA
Forward current (peak) 1/100Duty cycle 10us pulse width	i _{FS}	1	A
Power dissipation	P _T	100	mW
Operating temperature	T _A	-40 ~ +85	°C
Storage temperature	T _{stg}	-40 ~ +85	
Lead solder temperature [2mm below package base]	260°C For 5 Seconds		

Operating Characteristics (T _A =25°C)		THI/850 (GaAlAs)	Unit
Forward voltage (typ.) (I _F =20mA)	V _F	1.4	V
Forward voltage (max.) (I _F =20mA)	V _F	1.6	V
Reverse current (V _R =5V)	I _R	10	uA
Wavelength at peak emission (I _F =20mA)	λ _{peak}	850	nm
Spectral Line half-width (I _F =20mA)	Δλ	50	nm
Capacitance (V _F =0V, f=1MHz)	C	30	pF

Part Number	Emitting Material	Lens-color	Luminous Intensity (I _F =20mA*50mA) mW/sr		Wavelength nm λ _P	Viewing Angle 2θ1/2
			min.	typ.		
XTHI30BF850	GaAlAs	Blue Transparent	7 *10	15 *43	850	50°

XTHI30BF850



❖THI/850

